

PHPT61006PY

100 V, 6 A PNP high power bipolar transistor

21 January 2015

Product data sheet

1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT61006NY

2. Features and benefits

- High thermal power dissipation capability
- High temperature applications up to 175 °C
- Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-100	V
I _C	collector current		-	-	-6	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse	-	-	-12	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -6 A; I_B = -600 mA; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C; pulsed	-	85	270	mΩ



100 V, 6 A PNP high power bipolar transistor

Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		в—
3	Е	emitter	q	1%
4	В	base	وققق	sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

Ordering information

Table 3. **Ordering information**

Type number	Package				
	Name	Description	Version		
PHPT61006PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61006PY	1006PAB

2/16

100 V, 6 A PNP high power bipolar transistor

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-100	V
V _{CEO}	collector-emitter voltage	open base		-	-100	V
V _{EBO}	emitter-base voltage	open collector		-	-8	V
I _C	collector current			-	-6	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	-12	Α
I _B	base current			-	-1	Α
I _{BM}	peak base current	t _p ≤ 1 ms; pulsed		-	-2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.3	W
			[2]	-	3.3	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

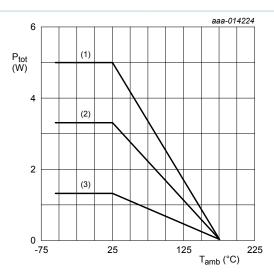
^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 6 cm².

^[3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

^[4] Power dissipation from junction to mounting base.

100 V, 6 A PNP high power bipolar transistor



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uig-a)	thermal resistance	in free air	[1]	-	-	115	K/W
	from junction to		<u>[2]</u>	-	-	45	K/W
	ambient		[3]	-	-	30	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

4/16

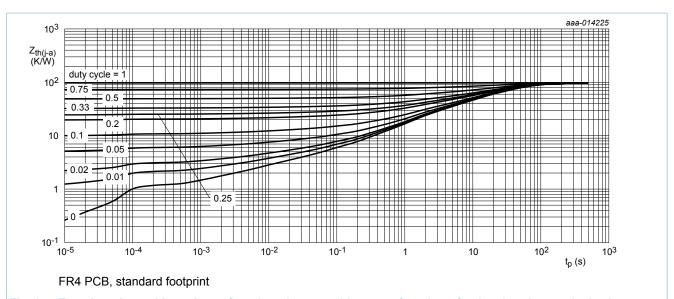


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

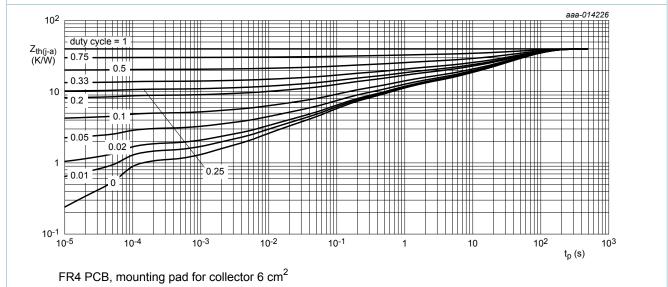


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

100 V, 6 A PNP high power bipolar transistor

10. Characteristics

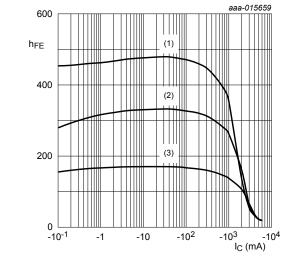
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -80 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
	current	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = -80 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -8 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -500 mA; T_{amb} = 25 °C	170	305	-	
		V_{CE} = -2 V; I_{C} = -1 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	160	275	-	
		V_{CE} = -2 V; I_{C} = -3 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	45	90	-	
		V_{CE} = -2 V; I_{C} = -6 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	10	20	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -1 A; I_{B} = -50 mA; t_{p} ≤ 300 µs; δ ≤ 0.02; T_{amb} = 25 °C	-	-75	-130	mV
		I_{C} = -3 A; I_{B} = -300 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C$	-	-150	-240	mV
		I_{C} = -6 A; I_{B} = -600 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	-900	-1600	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -6 A; I_{B} = -600 mA; t_{p} ≤ 300 µs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	-	85	270	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -1 A; I_B = -50 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-0.8	-0.95	V
		I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-0.95	-1.1	V
		I_{C} = -6 A; I_{B} = -600 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C$	-	-1.1	-1.25	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -500 mA; T_{amb} = 25 °C	-	-0.7	-0.8	V
t _d	delay time	V_{CC} = -12.5 V; I_C = -3 A;	-	15	-	ns
t _r	rise time	$I_{Bon} = -150 \text{ mA}; I_{Boff} = 150 \text{ mA};$	-	220	-	ns
t _{on}	turn-on time	T _{amb} = 25 °C	-	235	-	ns
t _s	storage time		-	160	-	ns
t _f	fall time		-	185	-	ns
t _{off}	turn-off time		-	345	-	ns

PHPT61006PY

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -500 mA; f = 100 MHz; T_{amb} = 25 °C	-	116	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	52	-	pF



$$V_{CE}$$
 = -2 V

(1)
$$T_{amb}$$
 = 100 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 4. DC current gain as a function of collector current; typical values

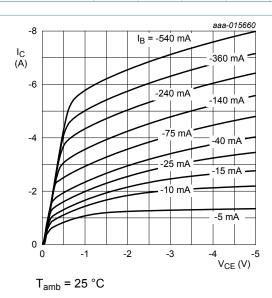
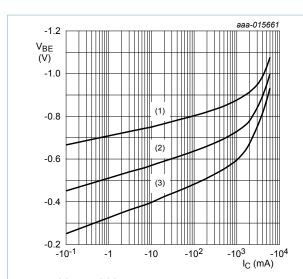


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



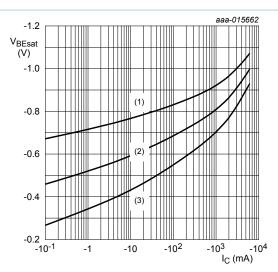
$$V_{CE}$$
 = -2 V

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



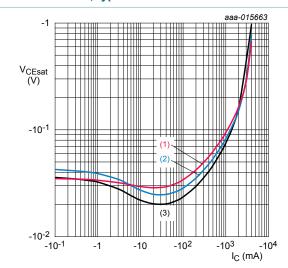
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



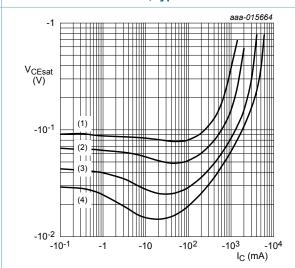
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



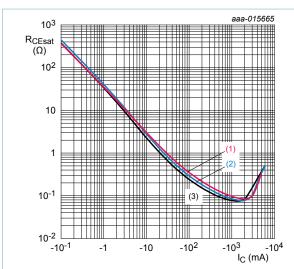
(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 20$$

$$(4) I_{C}/I_{B} = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



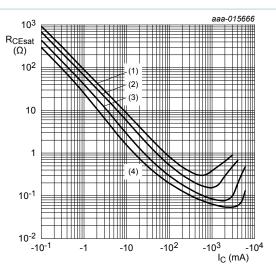
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

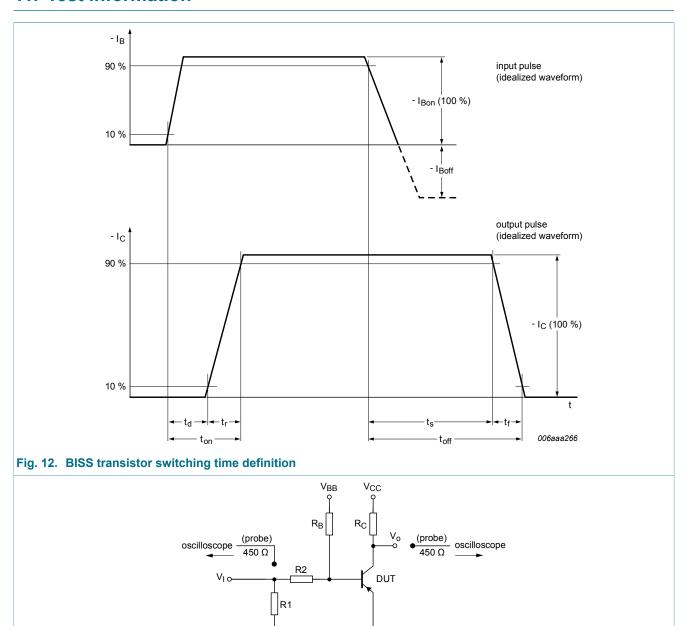
(3)
$$I_C/I_B = 20$$

(4)
$$I_C/I_B = 10$$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

100 V, 6 A PNP high power bipolar transistor

11. Test information



11.1 Quality information

Fig. 13. Test circuit for switching times

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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100 V, 6 A PNP high power bipolar transistor

12. Package outline

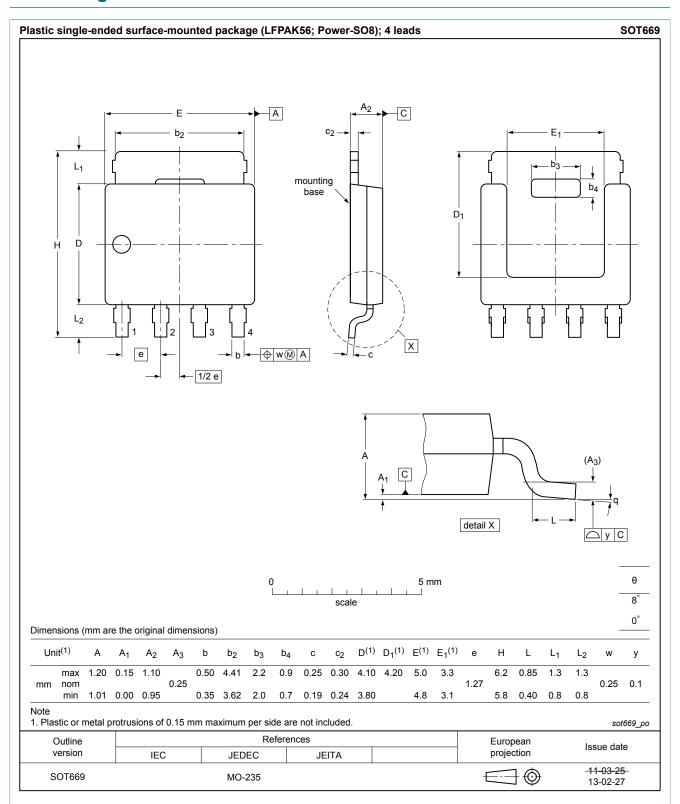


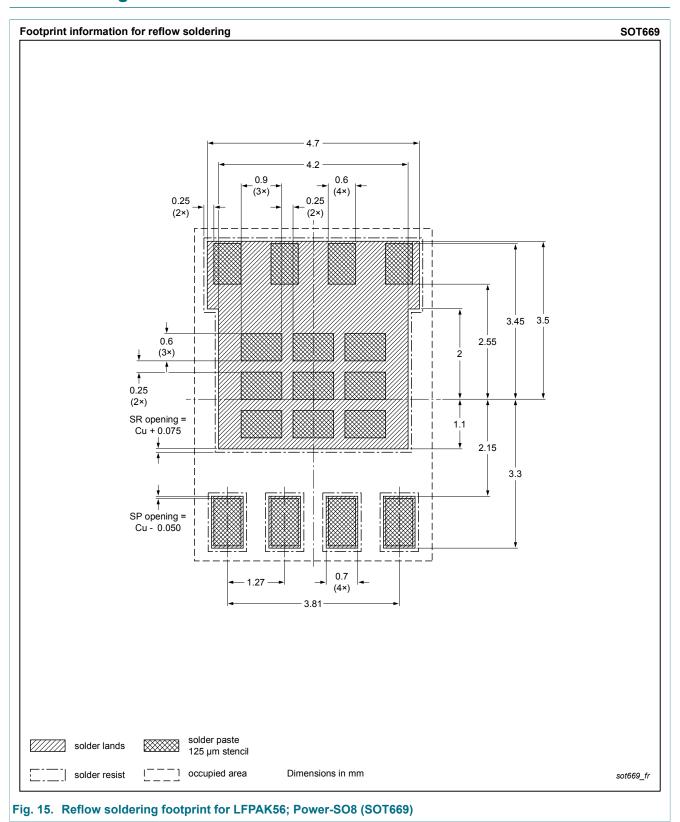
Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Soldering



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100 V, 6 A PNP high power bipolar transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61006PY v.1	20150121	Product data sheet	-	-

100 V, 6 A PNP high power bipolar transistor

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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100 V, 6 A PNP high power bipolar transistor

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100 V, 6 A PNP high power bipolar transistor

16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	10
11.1	Quality information	10
12	Package outline	11
13	Soldering	12
14	Revision history	13
15	Legal information	14
15.1	Data sheet status	14
15.2	Definitions	14
15.3	Disclaimers	14
15.4	Trademarks	15

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16/16